

Please replace the last full paragraph starting with "Recently," on page 1 of the specification with the following amended paragraph.

Recently, the transistor structure of the semiconductor integrated circuit has been further refined. Since the channel length of a transistor is shortened, the fluctuation width of the threshold voltage of the transistor is increased due to a short channel effect. The threshold voltage of the transistor varies, depending on the manufacturing conditions of the semiconductor integrated circuit, the chip position on the wafer, and the wafer position of production lots. If the fluctuation width of the threshold voltage is increased, deviation of inactivation timings of the power-on reset signal is also increased.

Please replace the paragraph starting on line 26 of page 4 of the specification with the following amended paragraph.

Fig. 5 is a block diagram showing a power-on resetting circuit in a third embodiment of the semiconductor integrated circuit in the present invention.

Please replace the last full paragraph starting on line 25, page 9, of the specification with the following amended paragraph.

The power-on resetting circuit is provided with two sub reset signal generators 10 and 12 and a main reset signal generator 36. The main reset signal generator 36 has pulse generators 16 and 18 respectively corresponding to the sub reset signal generators 10 and 12, a pulse generator 38 that receives a power-on reset signal PORE from the exterior of the power-on resetting circuit, and a composite circuit 40 that receives outputs of the pulse generators 16, 18 and 38.